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74AUP1G17

SINGLE SCHMITT-TRIGGER BUFFER

Description

The Advanced, Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The AUP1G17 is a single, one-input, Schmitt-Trigger buffer gate with a push-pull output designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down.

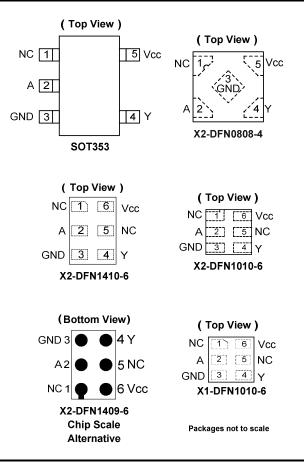
The gate performs the positive Boolean function:

 $\mathsf{Y} = \mathsf{A}$

Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption
 - lcc < 0.9μA
- Low Dynamic Power Consumption C_{PD} = 6pF (Typical at 3.6)
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250mV at Vcc = 3.0V.
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
 2000-V Human Body Model (A114)
 Exceeds 1000-V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments



Applications

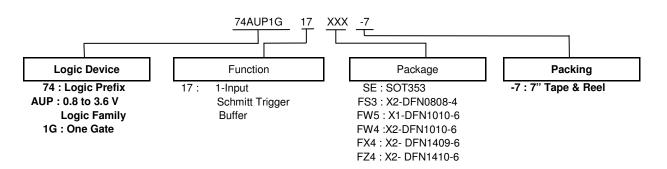
- Suited for Battery and Low Power Needs
- Wide array of products such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks
 - Computer Peripherals, Hard Drives, SSDs, CD/DVD ROMs
 - TVs, DVDs, DVRs, Set-Top Boxes

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information



Device	Package	Package	Package	7" Tape	and Reel
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74AUP1G17SE-7	SE	SOT353	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7
74AUP1G17FS3-7	FS3	X2-DFN0808-4	0.8mm x 0.8mm x 0.35mm 0.5 mm pad pitch (diamond)	5,000/Tape & Reel	-7
74AUP1G17FW5-7	FW5	X1-DFN1010-6	1.0mm x 1.0mm x 0.5mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G17FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G17FX4-7	FX4	X2-DFN1409-6 Chip Scale Alternative	1.4mm x 0.9mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G17FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7

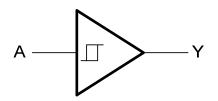
Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Function
NC	No Connection
A	Data Input
GND	Ground
Y	Data Output
Vcc	Supply Voltage

Logic Diagram



Function Table

Inputs	Output
Α	Y
Н	Н
L	L



Absolute Maximum Ratings (Notes 6 & 7) (@T_A = +25 °C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I < 0	50	mA
Ι _{ΟΚ}	Output Clamp Current (V _O < 0)	50	mA
lo	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8) (@T_A = +25 °C, unless otherwise specified.)

Symbol		Parameter	Min	Мах	Unit
V _{CC}	Operating Voltage		0.8	3.6	v
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
		$V_{CC} = 0.8V$	—	-20	μA
	I _{OH} High-Level Output Current	$V_{CC} = 1.1V$	—	-1.1	
		$V_{CC} = 1.4V$	—	-1.7	
ЮН		$V_{CC} = 1.65V$	—	-1.9	mA
		$V_{CC} = 2.3V$	—	-3.1	
		$V_{CC} = 3.0V$	—	-4	
		$V_{CC} = 0.8V$	—	20	μA
		$V_{CC} = 1.1V$	—	1.1	
		$V_{CC} = 1.4V$	—	1.7	
IOL	Low-Level Output Current	V _{CC} = 1.65V	—	1.9	mA
		$V_{CC} = 2.3V$	—	3.1	1
		$V_{CC} = 3.0V$	_	4	7
TA	Operating Free-Air Temperature		-40	125	°C

Note: 8. Unused inputs should be held at $V_{\mbox{\scriptsize CC}}$ or Ground.



Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Vaa	T _A = +	+25℃	T _A = -40 °C	Cto+85℃	Unit	
Symbol	Parameter	rest conditions	Vcc	Min	Max	Min	Max		
			0.8V	0.4	0.65	0.4	0.65		
			1.1V	0.53	0.9	0.53	0.9		
V-	Positive-Going Input Threshold		1.4V	0.74	1.11	0.74	1.11	v	
V_{T+}	Voltage	_	1.65V	0.91	1.29	0.91	1.29	v	
			2.3V	1.37	1.77	1.37	1.77		
			3.0V	1.61	2.32	1.61	2.32		
			0.8V	0.15	0.4	0.15	0.4		
	Negative-Going		1.1V	0.26	0.65	0.26	0.65		
V _{T-}	Input Threshold	_	1.4V	0.39	0.75	0.39	0.75	v	
	Voltage		1.65V	0.47	0.84	0.47	0.84		
			2.3V	0.69	1.04	0.69	1.04		
			3.0V	0.88	1.24	0.88	1.24		
			0.8V	0.07	0.5	0.07	0.5	-	
			1.1V	0.08	0.46	0.08	0.46		
ΔV_T	Hysteresis	_	1.4V	0.18	0.56	0.18	0.56	v	
	(V _{T+} - V _{T-)}		1.65V	0.27	0.66	0.27	0.66		
			2.3V	0.53	0.92	0.53	0.92		
			3.0V	0.79	1.31	0.79	1.31		
		I _{OH} = -20µА	0.8V to 3.6V	V _{CC} -0.1	—	V _{CC} -0.1			
		I _{OH} = -1.1mA	1.1V	0.75 x V _{CC}	—	0.7 x V _{CC}	—		
		I _{OH} = -1.7mA	1.4V	1.11	—	1.03	—		
Maria	High-Level	I _{OH} = -1.9mA	1.65V	1.32	—	1.30	—	v	
VOH	Output Voltage	I _{OH} = -2.3mA	0.01/	2.05	—	1.97	—	v	
		I _{OH} = -3.1mA	2.3V	1.9	—	1.85	—		
		I _{OH} = -2.7mA	2) (2.72		2.67	_		
		I _{OH} = -4mA	- 3V	2.6	_	2.55			
		I _{OL} = 20μΑ	0.8V to 3.6V	_	0.1	_	0.1		
		$I_{OL} = 1.1 \text{mA}$	1.1V	_	0.3 x V _{CC}	_	0.3 x V _{CC}		
		I _{OL} = 1.7mA	1.4V	—	0.31	—	0.37	-	
	Low-Level Output		1.65V	_	0.31	_	0.35		
VOL	Voltage	$I_{OL} = 2.3 \text{mA}$		_	0.31		0.33	V	
		$I_{OL} = 3.1 \text{mA}$	2.3V	_	0.44		0.45		
		$I_{OL} = 2.7 \text{mA}$			0.31		0.33	1	
		$I_{OL} = 4mA$	3V		0.44		0.45	-	
1.	Input Current	$V_1 = GND$ to 3.6V	0V to 3.6V		± 0.1		± 0.5	μA	
I _I I _{OFF}	Power Down Leakage Current	$V_{\rm I}$ or $V_{\rm O}$ = 0V to 3.6V	0 0 0 0 0 0		± 0.1		± 0.5	μA	
Δl _{OFF}	Delta Power Down Leakage Current	$V_{\rm I}$ or $V_{\rm O}$ = 0V to 3.6V	0V to 0.2V	_	± 0.2	_	± 0.6	μA	
Icc	Supply Current	$V_{I} = GND \text{ or } V_{CC}, I_{O} = 0$	0.8V to 3.6V	_	0.5	_	0.9	μA	
ΔI _{CC}	Additional Supply Current	Input at V_{CC} -0.6V	3.3V		40		50	μA	



Electrical Characteristics (continued) (@T_A = +25 °C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Ver	T _A = -40 °C	C to +125℃	Unit	
Бушрог	Parameter	Test Conditions	Vcc	Min	Max		
			0.8V	0.4	0.65		
			1.1V	0.53	0.9		
V_{T+}	Positive-Going Input Threshold	_	1.4V	0.74	1.11	- v	
V +	Voltage		1.65V	0.91	1.29	•	
	-		1.37	1.77			
			3.0V	1.61	2.32		
			0.8V	0.15	0.4	_	
	Negative-Going		1.1V	0.26	0.65	_	
V _T -	Input Threshold	_	1.4V	0.39	0.75	- V	
	Voltage		1.65V	0.47	0.84	_	
			2.3V	0.69	1.04	-	
			3.0V	0.88	1.24		
			0.8V	0.07	0.5	4	
	-luctorocio		1.1V 1.4V	0.08	0.46	4	
ΔV_{T}	Hysteresis (V _{T+} - V _{T-)}	—	1.4V 1.65V	0.18	0.56	- V	
	(• 1+ - • 1-)		2.3V	0.53	0.88	-	
					3.0V	0.79	1.31
		I _{OH} = -20µА	0.8V to 3.6V	V _{CC} – 0.11			
		$I_{OH} = -1.1 \text{mA}$	1.1V	0.6 x V _{CC}		-	
			1.4V	0.93		-	
		$I_{OH} = -1.7 \text{mA}$	1.65V	1.17		-	
VOH	High-Level Output Voltage	I _{OH} = -1.9mA	1.03V	1.77		- V	
	Output Voltage		2.3V		—	-	
		I _{OH} = -3.1mA		1.67	—	-	
		I _{OH} = -2.7mA	ЗV	2.40	—	_	
		I _{OH} = -4mA		2.30	—		
		l _{OL} = 20μA	0.8V to 3.6V	_	0.11		
		I _{OL} = 1.1mA	1.1V		0.33 x V _{CC}		
		I _{OL} = 1.7mA	1.4V	_	0.41		
Va	Low-Level Output	I _{OL} = 1.9mA	1.65V	—	0.39	v	
VOL	Voltage	I _{OL} = 2.3mA	0.01/	_	0.36	v	
		I _{OL} = 3.1mA	2.3V		0.50]	
		I _{OL} = 2.7mA		_	0.36	1	
		I _{OL} = 4mA	3V	_	0.50	1	
h	Input Current	$V_I = GND \text{ to } 3.6V$	0V to 3.6V		± 0.75	μA	
I _{OFF}	Power Down Leakage Current	$V_{\rm I}$ or $V_{\rm O} = 0$ V to 3.6V	0		± 3.5	μA	
Δl _{OFF}	Delta Power	V_{I} or $V_{O} = 0V$ to 3.6V	0V to 0.2V		± 2.5	μΑ	
I _{CC}	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μΑ	
Δlcc	Additional Supply Current	Input at V _{CC} -0.6V	3.3V		75	μA	



Switching Characteristics

C _L =5pF, See	Figure 1										
Parameter	From TO		Vee	Т	T _A = +25℃			T _A = -40 ℃ to +85 ℃		T _A = -40 ℃ to +125 ℃	
Farameter	Input	OUTPUT	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	—	19.0	-	—	_	—	—	
		Y	1.2V ± 0.1V	2.6	5.7	10.6	2.5	10.9	2.5	11.1	
	A or B		1.5V ± 0.1V	2.4	4.2	6.5	2.3	7.1	2.3	7.4	
t _{pd}	AUD		1.8V ± 0.15V	2.0	3.6	5.5	1.9	6.1	1.9	6.3	ns
			2.5V ± 0.2V	1.9	3.0	4.2	1.8	4.6	1.8	4.8]
			3.3V ± 0.3V	1.5	2.7	3.6	1.5	3.8	1.5	4.0	

CL=10pF, See Figure 1

Parameter	From	To Output	Vcc	T _A = +25 ℃			T _A = -40 ℃ to +85 ℃		T _A = -40 ℃ to +125 ℃		Unit
Faranielei	Input		V CC	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	22.5	_	—	_	—	_	
		Y	1.2V ± 0.1V	2.9	6.6	12.4	2.7	12.9	2.7	13.0	
	A or B		1.5V ± 0.1V	2.6	4.8	7.8	2.4	8.3	2.4	8.7	
t _{pd}	AUD		1.8V ± 0.15V	2.5	4.2	6.3	2.4	6.8	2.4	7.1	ns
			2.5V ± 0.2V	2.3	3.5	4.8	2.1	5.3	2.1	5.6	
			3.3V ± 0.3V	1.9	3.3	4.4	1.9	4.6	1.9	4.8	

CL=15pF, See Figure 1

Parameter	From Input	To Output	V _{cc}	T _A = +25 ℃			T _A = -40 ℃ to +85 ℃		T _A = -40 ℃ to +125 ℃		Unit
Faranieler			V CC	Min	Тур	Max	Min	Max	Min	Max	Onit
			0.8V	_	26.0	—		—	—	—	
			1.2V ± 0.1V	3.2	7.4	14.1	3.1	14.7	3.1	14.9	ns
	A or B	V	1.5V ± 0.1V	3.1	5.4	8.7	2.8	9.5	2.8	9.9	
t _{pd}	AUD	Ť	1.8V ± 0.15V	2.7	4.7	7.1	2.7	7.8	2.7	8.2	
			2.5V ± 0.2V	2.6	4.0	5.6	2.5	6.0	2.5	6.3	
			3.3V ± 0.3V	2.1	3.7	4.9	2.1	5.2	2.1	5.5	

CL=30pF, See Figure 1

Parameter	From Input	To Output	Vcc	T _A = +25 ℃			T _A = -40 ℃ to +85 ℃		T _A = -40 ℃ to +125 ℃		Unit
			V CC	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V		36.3		_	—	—	—	
		ВҮ	1.2V ± 0.1V	3.9	9.7	19.0	3.7	19.8	3.7	20.1	
.	A or B		1.5V ± 0.1V	3.5	7.0	11.2	3.6	12.4	3.6	13.0	
t _{pd}	AUD		1.8V ± 0.15V	3.5	6.0	9.2	3.4	10.1	3.4	10.7	ns
			2.5V ± 0.2V	3.4	5.1	7.0	3.2	7.5	3.2	7.9	
			3.3V ± 0.3V	2.5	4.8	6.2	2.5	7.1	2.5	7.5	



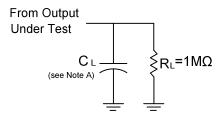
Operating and Package Characteristics (@T_A = +25 °C, unless otherwise specified.)

	Parameter	Test Conditio	ons	V _{cc}	Тур	Unit
				0.8V	6.5	
				1.2V ± 0.1V	6.3	
<u> </u>	Power Dissipation	f = 1MH	lz	1.5V ± 0.1V	6.3	рF
C _{pd}	Capacitance	No Loa	d	1.8V ± 0.15V	6.2	рг
				2.5V ± 0.2V	6.2	
				3.3V ± 0.3V	6.1	
Ci	Input Capacitance	V _i = V _{CC} or	$V_i = V_{CC} \text{ or } GND$		1.5	pF
		SOT353		_	371	
		X2-DFN0808-4		_	430	
0	Thermal Resistance	X1-DFN1010-6	(Note 0)	_	435	°C/W
θ _{JA}	Junction-to-Ambient	X2-DFN1010-6	(Note 9)	_	445	°C/W
		X2-DFN1409-6		—	470	
		X2-DFN1410-6		—	460	
		SOT353		—	143	
		X2-DFN0808-4		—	240	
0	Thermal Resistance	X1-DFN1010-6	(Niete O)	—	250	0C AM
θ _{JC}	Junction-to-Case	X2-DFN1010-6	(Note 9)	—	250	°C/W
		X2-DFN1409-6]	_	275	
		X2-DFN1410-6]		265	

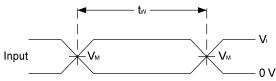
Note: 9. Test condition for each of the six package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



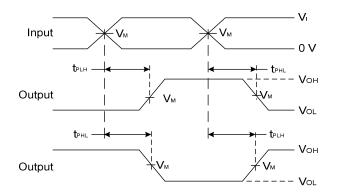
Parameter Measurement Information



Vcc	Inputs		V	0
VCC	VI	t _r /t _f	V _M	CL
0.8V	Vcc	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V±0.1V	Vcc	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V±0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ±0.15V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V±0.2V	Vcc	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V±0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

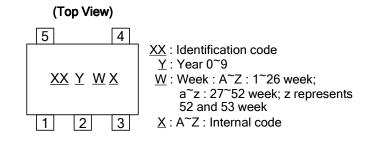
- Notes: A. Includes test lead and test apparatus capacitance. B. All pulses are supplied at pulse repetition rate ≤ 10MHz.

 - C. Inputs are measured separately one transition per measurement.
 - D. tPLH and tPHL are the same as tPD.



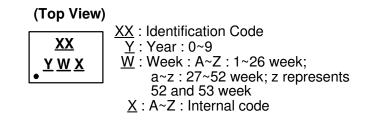
Marking Information

(1) SOT353



Part Number	Package	Identification Code	
74AUP1G17SE-7	SOT353	XT	

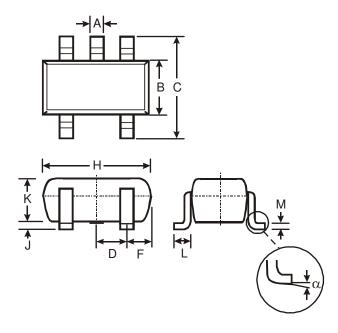
(2) X2-DFN0808-4, X1-DFN1010-6, X2-DFN1010-6, X2-DFN1409-6 and X2-DFN1410-6



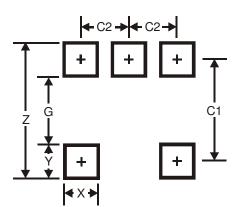
Part Number	Package	Identification Code
74AUP1G17FS3-7	X2-DFN0808-4	ΥT
74AUP1G17FW5-7	X1-DFN1010-6	QH
74AUP1G17FW4-7	X2-DFN1010-6	XT
74AUP1G17FX4-7	X2-DFN1409-6	HJ
74AUP1G17FZ4-7	X2-DFN1410-6	XT



SOT353 Package Outline Dimensions and Suggested Pad Layout



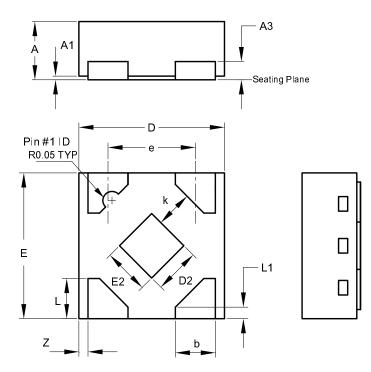
	SOT353				
Dim	Min	Max	Тур		
Α	0.10	0.30	0.25		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D	0.65 Typ				
F	0.40	0.45	0.425		
н	1.80	2.20	2.15		
J	0	0.10	0.05		
К	0.90	1.00	1.00		
L	0.25	0.40	0.30		
М	0.10	0.22	0.11		
α	0°	8°	-		
A	All Dimensions in mm				



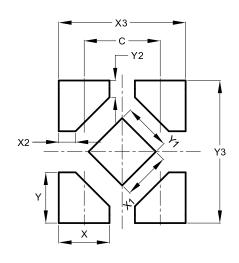
Dimensions	Value (in mm)	
Z	2.5	
G	1.3	
Х	0.42	
Y	0.6	
C1	1.9	
C2	0.65	



X2-DFN0808-4 Package Outline Dimensions and Suggested Pad Layout



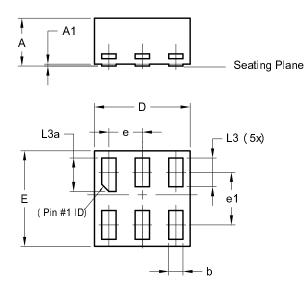
X2-DFN0808-4					
Dim	Min	Max	Тур		
Α	0.25	0.35	0.30		
A1	0	0.04	0.02		
A3	-	-	0.13		
b	0.17	0.27	0.22		
D	0.75	0.85	0.80		
D2	0.15	0.35	0.25		
E	0.75	0.85	0.80		
E2	0.15	0.35	0.25		
е	-	-	0.48		
k	0.20	-	-		
L	0.17	0.27	0.22		
L1	0.02	0.12	0.07		
z	-	-	0.05		
A	All Dimensions in mm				



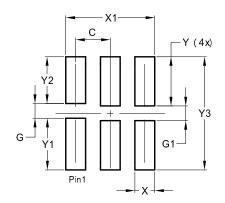
Dimensions	Value
С	0.480
X	0.320
X1	0.300
X2	0.106
X3	0.800
Y	0.320
Y1	0.300
Y2	0.106
¥3	0.900



X1-DFN1010-6 (Type B) Package Outline Dimensions and Suggested Pad Layout



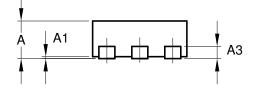
X1-DFN1010-6						
	(Type B)					
Dim	Min	Max	Тур			
Α	-	0.50	0.39			
A1	-	0.04	-			
b	0.12	0.20	0.15			
D	0.95	1.050	1.00			
E	0.95	1.050	1.00			
е		0.35 B	SC			
e1		0.55 B	SC			
L3	0.27	0.30	0.30			
L3a	0.32	0.40	0.35			
All	Dimen	All Dimensions in mm				

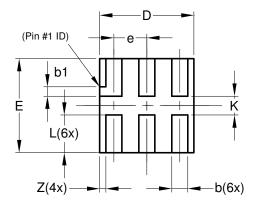


Dimensions	Value (in mm)	
С	0.350	
G	0.150	
G1	0.150	
X	0.200	
X1	0.900	
Y	0.500	
Y1	0.525	
Y2	0.475	
Y3	1.150	

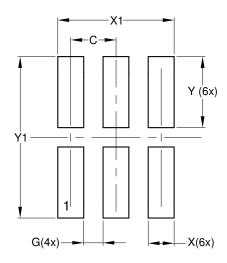


X2-DFN1010-6 Package Outline Dimensions and Suggested Pad Layout





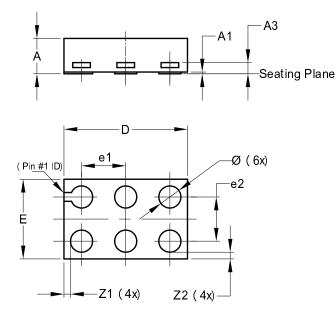
	X2-DFN1010-6				
Dim	Min	Max	Тур		
Α		0.40	0.39		
A1	0.00	0.05	0.02		
A3			0.13		
b	0.14	0.20	0.17		
b1	0.05	0.15	0.10		
D	0.95	1.05	1.00		
Е	0.95	1.05	1.00		
е			0.35		
L	0.35	0.45	0.40		
к	0.15				
Z			0.065		
All Dimensions in mm					



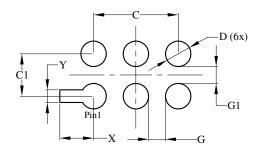
Dimensions	Value (in mm)	
С	0.350	
G	0.150	
X	0.200	
X1	0.900	
Y	0.550	
Y1	1.250	



X2-DFN1409-6 Package Outline Dimensions and Suggested Pad Layout



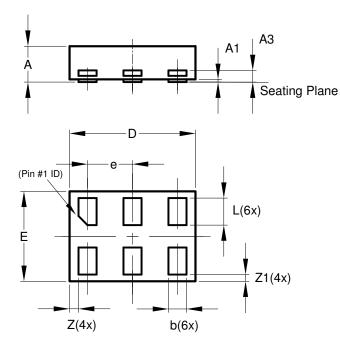
	X2-DFN1409-6				
Dim	Min	Max	Тур		
Α	-	0.40	0.39		
A1	0	0.05	0.02		
A3	-	-	0.13		
Ø	0.20	0.30	0.25		
D	1.35	1.45	1.40		
Е	0.85	0.95	0.90		
e1	-	-	0.50		
e2	-	-	0.50		
Z1	-	-	0.075		
Z2	-	-	0.075		
All [All Dimensions in mm				



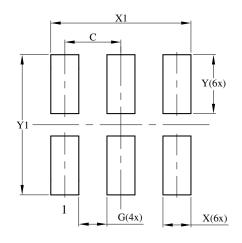
Dimensions	Value (in mm)	
С	1.000	
C1	0.500	
D	0.300	
G	0.200	
G1	0.200	
Х	0.400	
Y	0.150	



X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout



X2-DFN1410-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3			0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е			0.50	
L	0.25	0.35	0.30	
Z		_	0.10	
Z1	0.045	0.105	0.075	
All Dimensions in mm				



Dimensions	Value (in mm)	
С	0.500	
G	0.250	
Х	0.250	
X1	1.250	
Y	0.525	
Y1	1.250	



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